2018년 2월 7일(수), 13:15-14:45 Room F (봉래I, 6층)

F. Silicon and Group-IV Devices and Integration Technology 분과 [WF3-F] Photonics and Nanowire Technology

	Co-on-Insulator Structurousing V. O. for Mid-Infrared Photonics Platform
WF3-F-1 13:15-13:30	Ge-on-Insulator Structureusing Y ₂ O ₃ for Mid-Infrared Photonics Platform SangHyeon Kim ^{1,2} , Jae-Hoon Han ¹ , Jae-Phil Shim ³ , Hyung-Jun Kim ^{2,3} , and Won Jun Choi ¹ ¹ Center for Opto-Electronics Materials and Devices, KIST, ² Nanomaterials Science and Engineering, UST, ³ Center for Spintronics, KIST
WF3-F-2 13:30-13:45	High Concentration Phosphorous Doping in Ge for CMOS-Integrated Laser Applications Heedong Park ¹ , Motoki Yako ² , Yasuhiko Ishikawa ² , Kazumi Wada ^{2,3} , and Donghwan Ahn ¹ ¹ School of Materials Science and Engineering, Kookmin University, ² Department of Materials Engineering, University of Tokyo, ³ Department of Materials Science and Engineering, MIT
WF3-F-3 13:45-14:00	Si Fin/Si _{1-x} Ge _x Shell Channel <i>p</i> -Type FinFET for Sub-10-nm Technology Nodes and Its High-Speed Operation Eunseon Yu ¹ , Won-Jun Lee ² , Jongwan Jung ² , and Seongjae Cho ^{1,3} ¹ Graduate School of IT Convergence Engineering, Gachon University, ² Department of Nanotechnology and Advanced Materials Engineering, Sejong University, ³ Department of Electronics Engineering, Gachon University
WF3-F-4 14:00-14:15	Statistical Process-Induced Random Variation: Work-Function Variation in Stacked Nanowire FET Jinyoung Park and Changhwan Shin Department of Electrical and Computer Engineering, University of Seoul
WF3-F-5 14:15-14:30	A Characteristic of Stacked Gate-All-Around Nanowire MOSFET based on Source Drain Doping Profile Suhyeon Kim, Junil Lee, Myung-Hyun Baek, Sihyun Kim, Ryoongbin Lee, Hyun-Min Kim, Kitae Lee, and Byung-Gook Park Department of Electrical Engineering, Seoul National University
WF3-F-6 14:30-14:45	Simulation Study on the Effect of Unconformal Work-Function Metal Deposition on the Electrical Characteristic of Stacked-GAA MOSFET Sihyun Kim ¹ , Suhyeon Kim ¹ , Sangwan Kim ² , Euyhwan Park ¹ , Junil Lee ¹ , Ryoongbin Lee ¹ , Soyeon Kim ¹ , Hyun-Min Kim ¹ , Kitae Lee ¹ , Jong-Ho Lee ¹ , and Byung-Gook ¹ *ISRC and Department of Electrical and Computer Engineering, Seoul National University, *2Department of Electrical and Computer Engineering, Ajou University